

#### 30W, 28V, DC-4GHz, GaN RF Unmatched Transistor

#### **Product Overview**

The MCNPA0040-P30 is a 30W(P3dB) unmatched GaN amplifier which operates from DC to 4GHz with 28V rail, offers a general purpose,broadband,high power and high efficiency wireless pulse or CW communction application.

**ROHS** compliant

Evaluation boards are available upon request.



Figure1.

### **Functional Block Diagram**

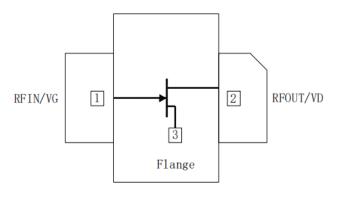


Figure2.

### **Pin Description**

Pin	Symbol	Description
1	RFIN/VG	RF input/Gate Bias
2	RFOUT/VD	RF output/Drain Voltage
3	GND	Grouding

#### **Key Features**

- Frequency Range: DC-4GHz
- Operating Drain Voltage: 28V
- 19dB small signal Gain @0.9GHz
- 16dBGain@45dBm,0.9GHz
- 46.5dBm CW Peak Power
- 70% Drain Efficiency @Psat,0.9GHz
- NI200 2 Lead flange Ceramic package (MSL3,260 per JEDEC J-STD-020)

### **Applications**

- 3GPP 4G LTE/5G NR massive MIMO basestation
- Driver amplifier for micro-base and macro-base and macro-base Stations
- Active antenna array
- Pico/Small Cell
- Test Instrumentation
- Industrial, scientific, and medical
- Wideband amplifiers

#### **Ordering info**

Part No.	Description		
MCNPA0040-P30SF	with Flange,7'Reel with 500pcs		
MCNPA0040-P30SN	without Flange, 7'Reel with 500pcs		



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#### Absolute Maximum Ratings<sup>1</sup>

Parameter	Rating	Unit
Operating Temp,Tc	-40 to +105	
Operating Junction Temp,TJ	225	
Storage Temp,TsTG	-55 to+125	
Thermal Resistance, R jc		/W
Operating Voltage,VDD	0 to 55	V
Drain-Source Voltage,VDSS	200	V
Gate-Source Voltage,VGS	-8 to 0	V
Maximum Forward Gate Current	10	mA
Inuput Power,PIN	+35	dBm

Notes<sup>1</sup>: Exceeding any one or a combination of the Absolute Maxium Rating conditions may cause permanent damage to the device. Extended application of the Absolute Maximum Rating conditions to the device mayreduce device reliability.

#### **Recommended Operating Conditions**

Parameter	Min	Тур	Max	Unit
Operating Frequency,F	DC		4	GHz
Operating Temp,Tc	-40	25	85	
Drain Voltage,VDD		28		V
Gate Voltage,VGS		-2.8		V
Quiescent Current,IDQ		50		mA

### Electrical Specifications-EVB Typical Performance<sup>1</sup>

Parameter	Conditions	Min	Тур	Max	Unit
Frequency			900		MHz
Output P3dB	CW		+46.5		dBm
Gain@45dBm	CW		16		dB
Drain efficiency@Psat	CW		70		%

Notes1:VD=28V,IDQ=50mA,TC=25 , Input/Output Load=50



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### **Package Marking and Dimensions**

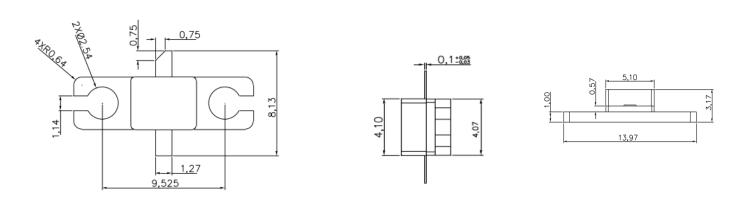


Figure 3.MCNPA0040-P30SF Package Dimensions

Notes:

- 1. All dimensions are in mm. Otherwise noted, the tolerance is ±0.13 mm.
- 2. LEAD FINISH AU ; FLANGE FINISH AU.

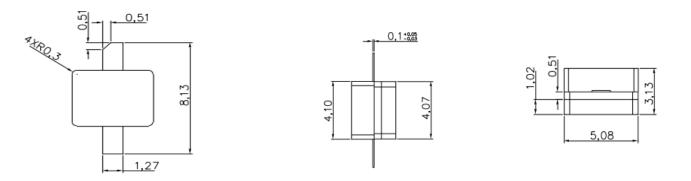


Figure 4. MCNPA0040-P30SN Package Dimensions

Notes:

- 1. All dimensions are in mm. Otherwise noted, the tolerance is ±0.13 mm.
- 2. LEAD FINISH AU.



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#### **Tape and Reel Information**

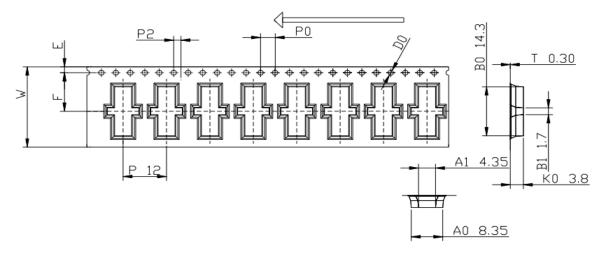


Figure 5.

- 1. The cumulative error range of 10 chain hole center distances is within in ±0.22mm
- 2.Reverse curvanture at 1mm/250mm
- 3.Material: Black PS material , compliant with ROHS environmental management substances
- 4.All dimensions meet the requirements of EIA-481-B
- 5.Thickness :0.3±0.55mm
- 6.Protective tape:Transparent PS material

### Evaluation board test procedure

#### Turn-on sequence

1.Connect test equipment to the input and output port of Evaluation board and then connect DC ground.

2.Turn on VG to -7V, turn on VD to 28V then tune VG to 80mA quiescent current in order.

3.Apply RF signal.

## Turn-off sequence

1.Turn off RF signal.
2.Turn off VD.
3.Turn off VG.